Ordering number : ENN8161

SANYO Semiconductors
DATA SHEET

N-Channel Silicon MOSFET

CPH3437 — General-Purpose Switching Device Applications

Features

- Low ON-resistance.
- Ultrahigh-speed switching.
- 2.5V drive.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		20	V
Gate-to-Source Voltage	V_{GSS}		±10	V
Drain Current (DC)	I_D		4.5	A
Drain Current (Pulse)	I_{DP}	PW≤10μs, duty cycle≤1%	18	A
Allowable Power Dissipation	P_D	Mounted on a ceramic board (900mm²×0.8mm)	1.0	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		−55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=1mA, V_{GS}=0	20			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=20V, V_{GS}=0			1	μA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=±8V, V_{DS}=0			±10	μA
Cutoff Voltage	V_{GS}(off)	V_{DS}=10V, I_D=1mA	0.4		1.4	V
Forward Transfer Admittance	|yfs|	V_{DS}=10V, I_D=2.5A	4	6.8		S
Static Drain-to-Source On-State Resistance	R_{DS}(on)1	I_D=2A, V_{GS}=4.5V		28	39	mΩ
	R_{DS}(on)2	I_D=2A, V_{GS}=4V		29	40	mΩ
	R_{DS}(on)3	I_D=1A, V_{GS}=2.5V		39	55	mΩ
Input Capacitance	Ciss	V_{DS}=10V, f=1MHz		755		pF
Output Capacitance	Coss	V_{DS}=10V, f=1MHz		155		pF
Reverse Transfer Capacitance	Crss	V_{DS}=10V, f=1MHz		135		pF
Turn-ON Delay Time	t_d(on)	See specified Test Circuit.		17		ns
Rise Time	t_r	See specified Test Circuit.		100		ns
Turn-OFF Delay Time	t_d(off)	See specified Test Circuit.		68		ns
Fall Time	t_f	See specified Test Circuit.		85		ns

Marking : ZM

Continued on next page.

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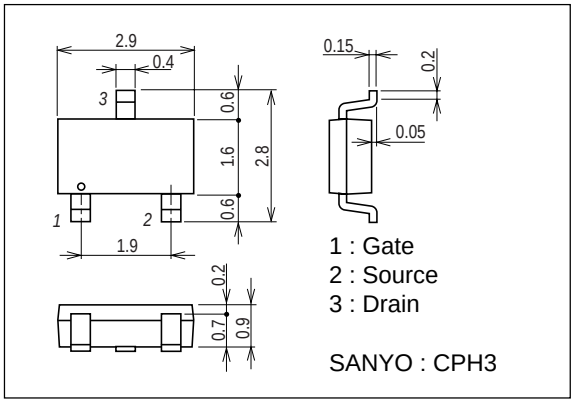
Continued from preceding page.

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Total Gate Charge	Qg	V_{DS}=10V, V_{GS}=4V, I_D=4.5A		9.9		nC
Gate-to-Source Charge	Qgs	V_{DS}=10V, V_{GS}=4V, I_D=4.5A		1.35		nC
Gate-to-Drain “Miller” Charge	Qgd	V_{DS}=10V, V_{GS}=4V, I_D=4.5A		3.5		nC
Diode Forward Voltage	V_{SD}	I_S=4.5A, V_{GS}=0		0.84	1.2	V

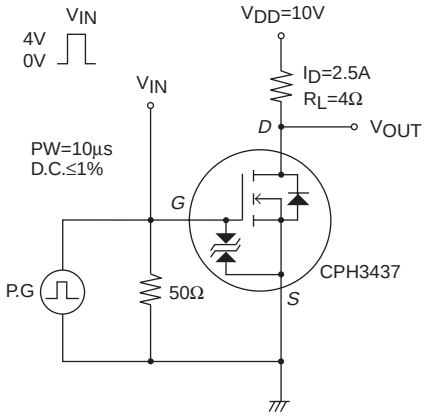
Package Dimensions

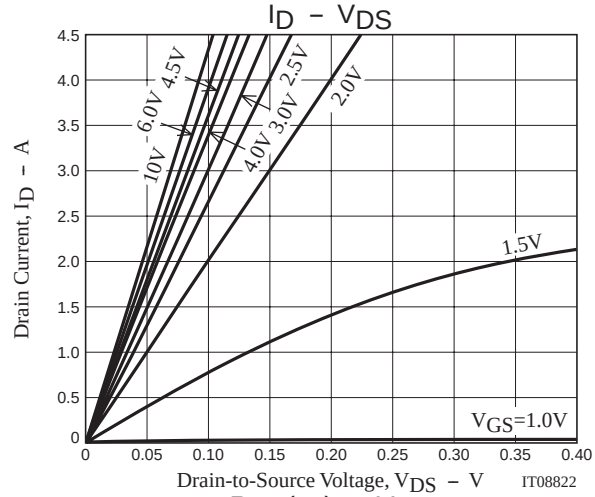
unit : mm

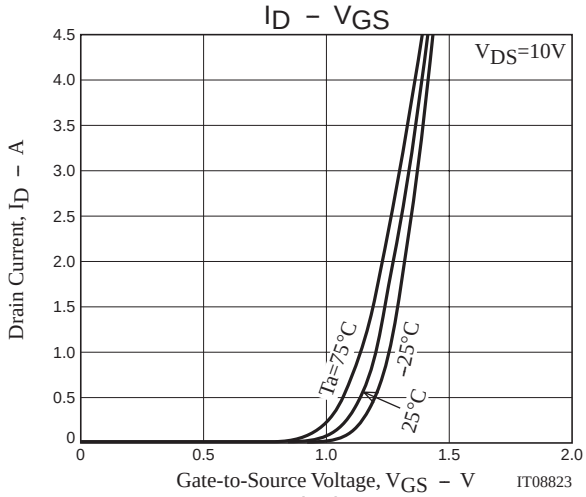
2152A

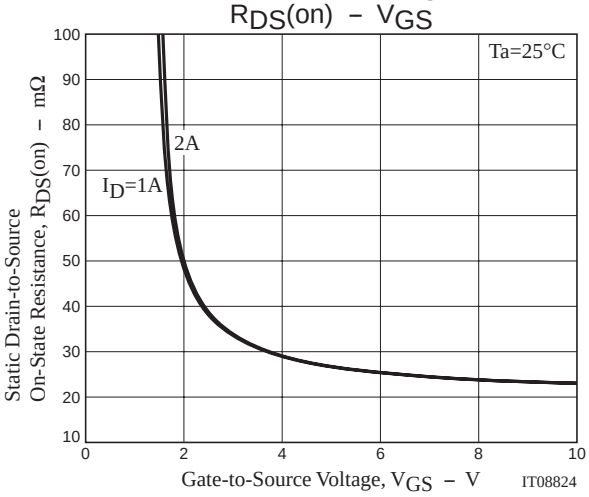


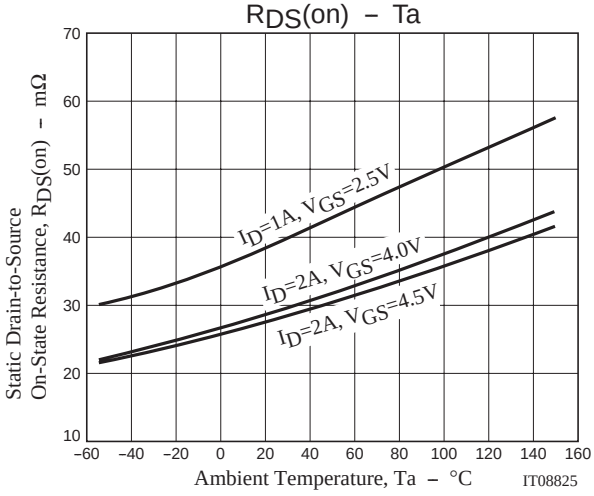
Switching Time Test Circuit

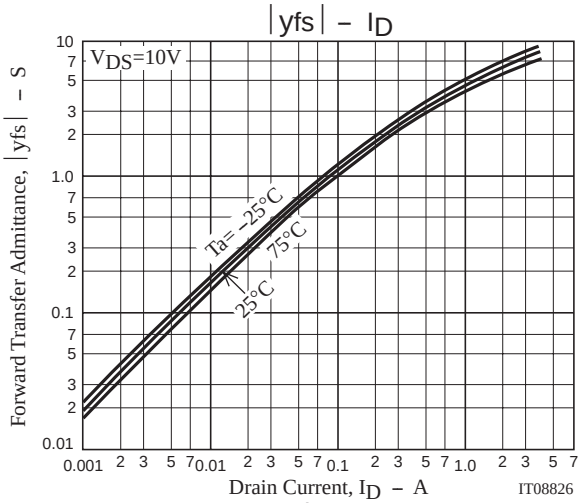


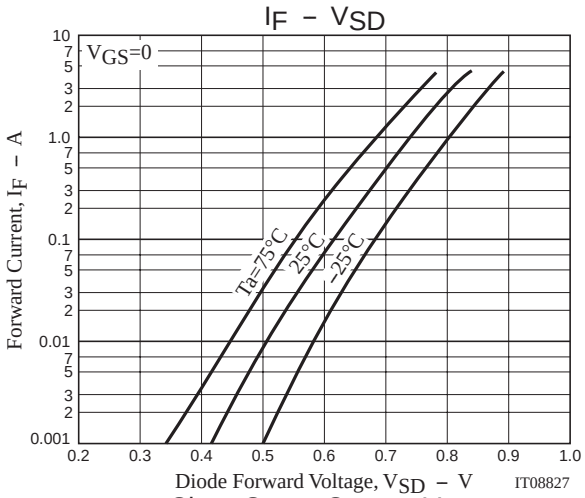


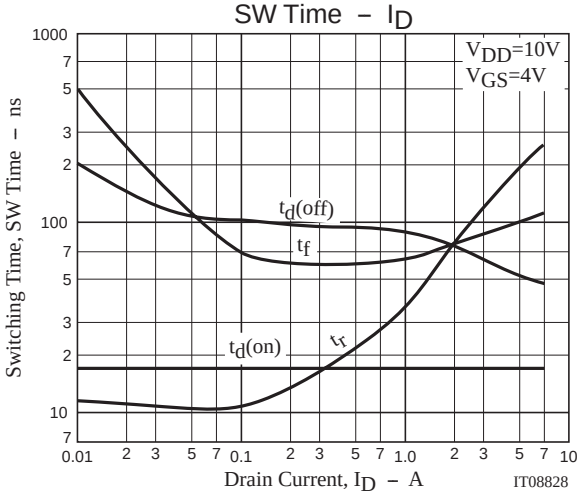


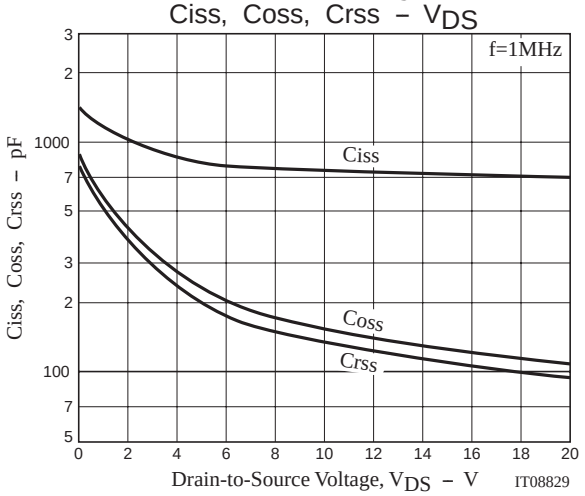


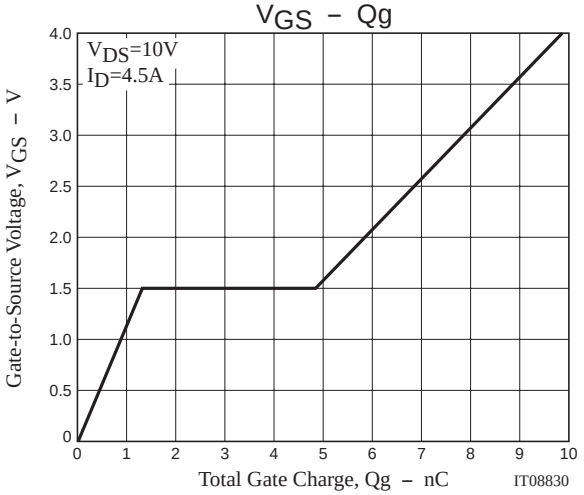


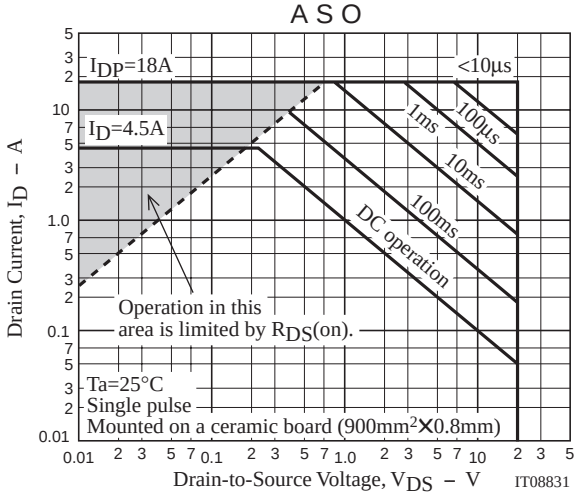

|yfs| – ID
VDS=10V
Ta= –25°C
25°C
75°C
Forward Transfer Admittance, |yfs| – S
Drain Current, ID – A
IT08826

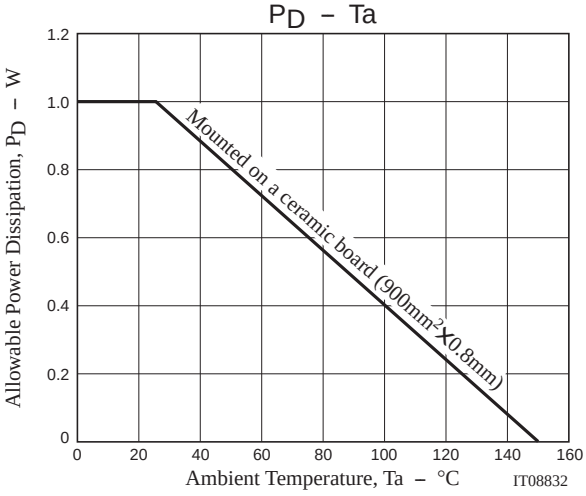

IF – VSD
VGS=0
Ta=75°C
25°C
–25°C
Forward Current, IF – A
Diode Forward Voltage, VSD – V
IT08827


SW Time – ID
VDD=10V
VGS=4V
td(off)
tf
td(on)
tr
Switching Time, SW Time – ns
Drain Current, ID – A
IT08828


Ciss, Coss, Crss – VDS
f=1MHz
Ciss
Coss
Crss
Ciss, Coss, Crss – pF
Drain-to-Source Voltage, VDS – V
IT08829


VGS – Qg
VDS=10V
ID=4.5A
Gate-to-Source Voltage, VGS – V
Total Gate Charge, Qg – nC
IT08830


A S O
IDP=18A
ID=4.5A
<10μs
1ms
100μs
10ms
100ms
DC operation
Operation in this
area is limited by RDS(on).
Ta=25°C
Single pulse
Mounted on a ceramic board (900mm2×0.8mm)
Drain Current, ID – A
Drain-to-Source Voltage, VDS – V
IT08831


PD – Ta
Mounted on a ceramic board (900mm2×0.8mm)
Allowable Power Dissipation, PD – W
Ambient Temperature, Ta – °C
IT08832

Note on usage : Since the CPH3437 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.